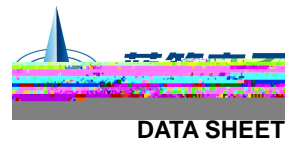


BRES5V0M1B2ZP

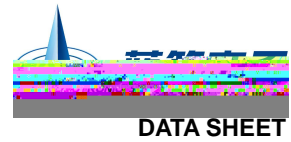
Rev.A Jun.-2021



A	2020.09.15	ALL	LX LS3206V5-1N		
A	2021-6-28	ALL	DFN1006A-2L DFN1006-2L		

BRESD5V0M1B2ZP

Rev.A Jun.-2021



/ Descriptions

DFN1006-2L ESD
DFN1006-2L Plastic Package 1-Line,Bi-directional , ESD Protection Diode.

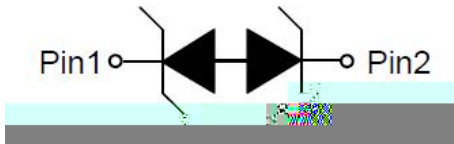
/ Features

- ◆ Stand-off voltage: $\pm 5V$ Max.
- ◆ Transient protection for each line according to
 - IEC61000-4-2(ESD): $\pm 30kV$ (contact)
 - IEC61000-4-4 (EFT): 80A (5/50ns)
 - IEC61000-4-5(surge): 20A (8/20 μs)
- ◆ Ultra-low capacitance: $C_J = 35pF$ typ.
- ◆ Low leakage current:
- ◆ Low clamping voltage: $V_{CL} = 7.8V$ typ. @ $I_{PP} = 16A$ (TLP)
- ◆ Solid-state silicon technology
- ◆ HF Product

/ Applications

- ◆ Battery Line Protection
- ◆ Audio Line Protection
- ◆ Microphone Line Protection
- ◆ GPIO Protection

/ Equivalent Circuit



/ Pinning



/ Marking

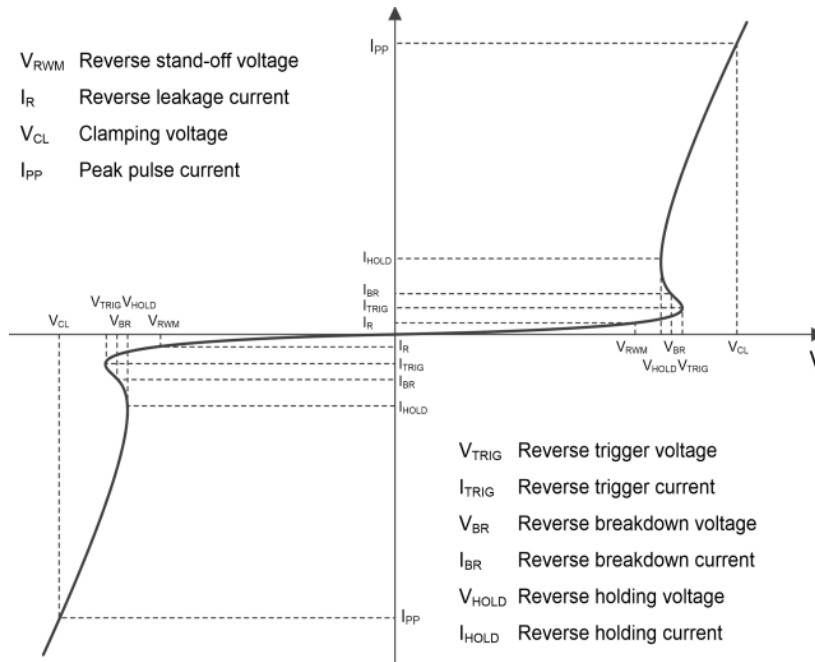
See Marking Instructions.



/ Absolute Maximum Ratings

参数 Parameter	符号 Symbol	数值 Rating	单位 Unit
Peak Pulse Power($t_p = 8/20\mu s$)	P_{PK}	230	W
Peak Pulse Current($t_p = 8/20\mu s$)	I_{PP}	20	A
ESD according to IEC61000-4-2 air discharge	V_{ESD}	± 30	KV
ESD according to IEC61000-4-2 contact discharge		± 30	
Junction temperature	T_J	125	$^{\circ}C$
Operating temperature	T_{OP}	-40~85	$^{\circ}C$
Lead temperature	T_L	260	$^{\circ}C$
Storage Temperature	T_{STG}	-55~+150	$^{\circ}C$

/ Electrical Characteristics(Ta=25)



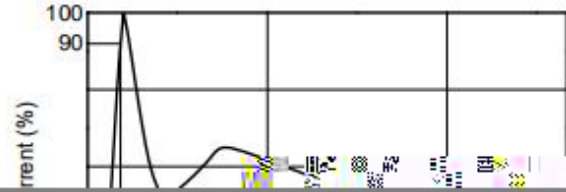
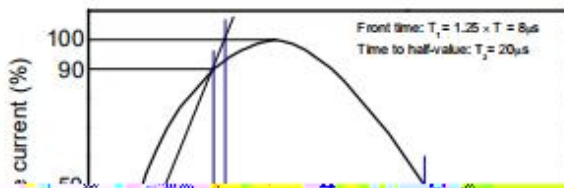
Definitions of electrical characteristics

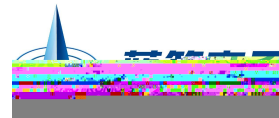
Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Reverse maximum working voltage	V_{RWM}				± 5.0	V
Reverse leakage current	I_R	$V_{RWM} = 5.0V$			100	nA
Reverse breakdown voltage	V_{BR}	$I_{BR}=1mA$	5.1			V
Reverse holding voltage	V_{HOLD}	$I_{HOLD}=50mA$	5.1			V
Clamping voltage ¹⁾	V_{CL}	$I_{PP}=16A \quad t_p=100ns$		7.8		V
Dynamic resistance ¹⁾	R_{DYN}			0.1		
Clamping voltage ²⁾	V_{CL}	$V_{ESD}= 8kV$		8.0		V
Clamping voltage ³⁾	V_{CL}	$I_{PP} = 1A \quad t_p = 8/20\mu s$		6.2	8	V
		$I_{PP} = 20A \quad t_p = 8/20\mu s$		9.5	11.5	V
Junction Capacitance	C_J	$V_R = 0V \quad f = 1MHz$		35	45	pF
	C_J	$V_R = 5V \quad f = 1MHz$		25	35	pF

Notes:

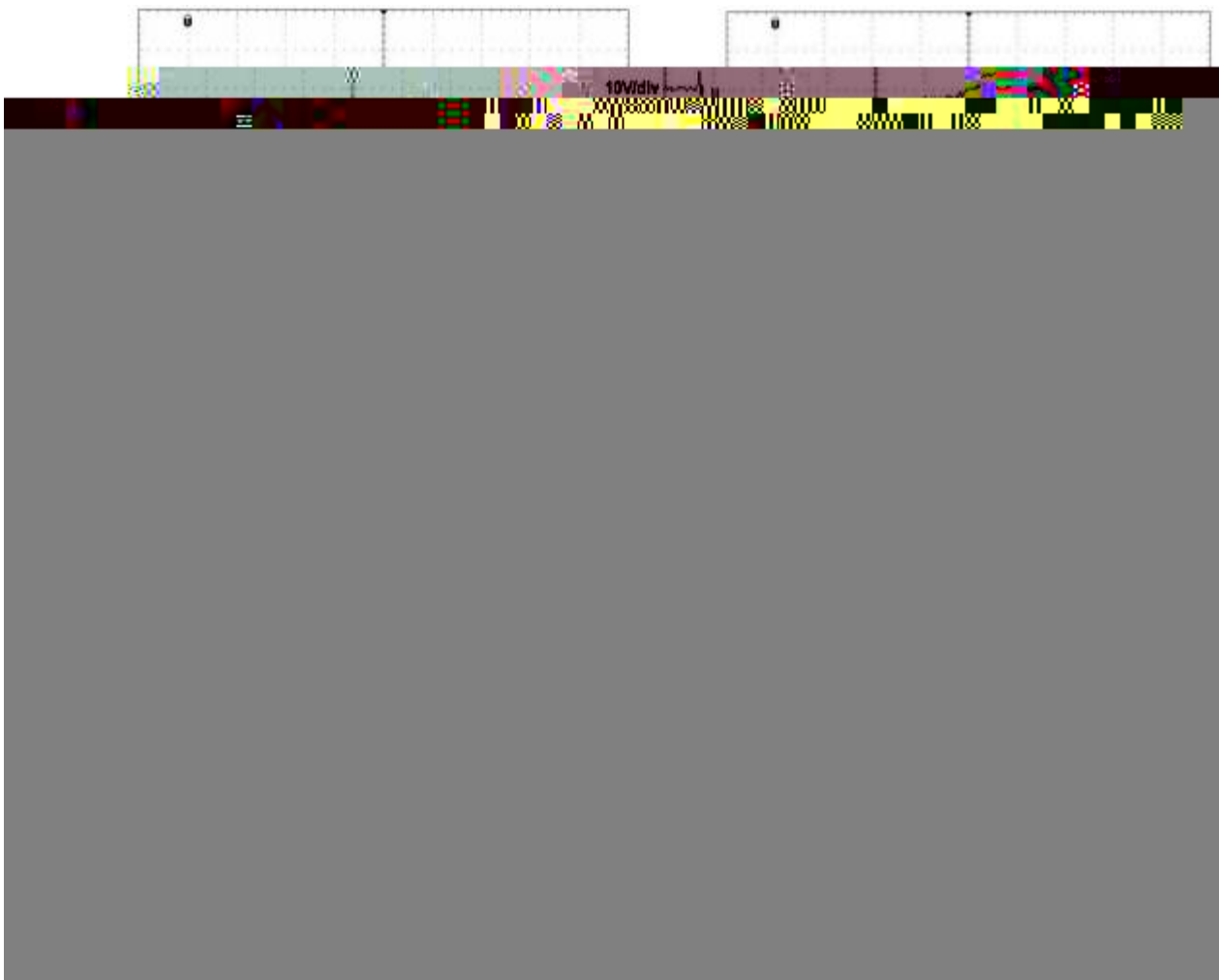
- 1) TLP parameter: $Z_0 = 50\Omega$, $t_p = 100ns$, $t_r = 2ns$, averaging window from 60ns to 80ns. R_{DYN} is calculated from 4A to 16A.
- 2) Contact discharge mode, according to IEC61000-4-2.
- 3) Non-repetitive current pulse, according to IEC61000-4-5.

/ **Electrical Characteristic Curve(Ta=25)**





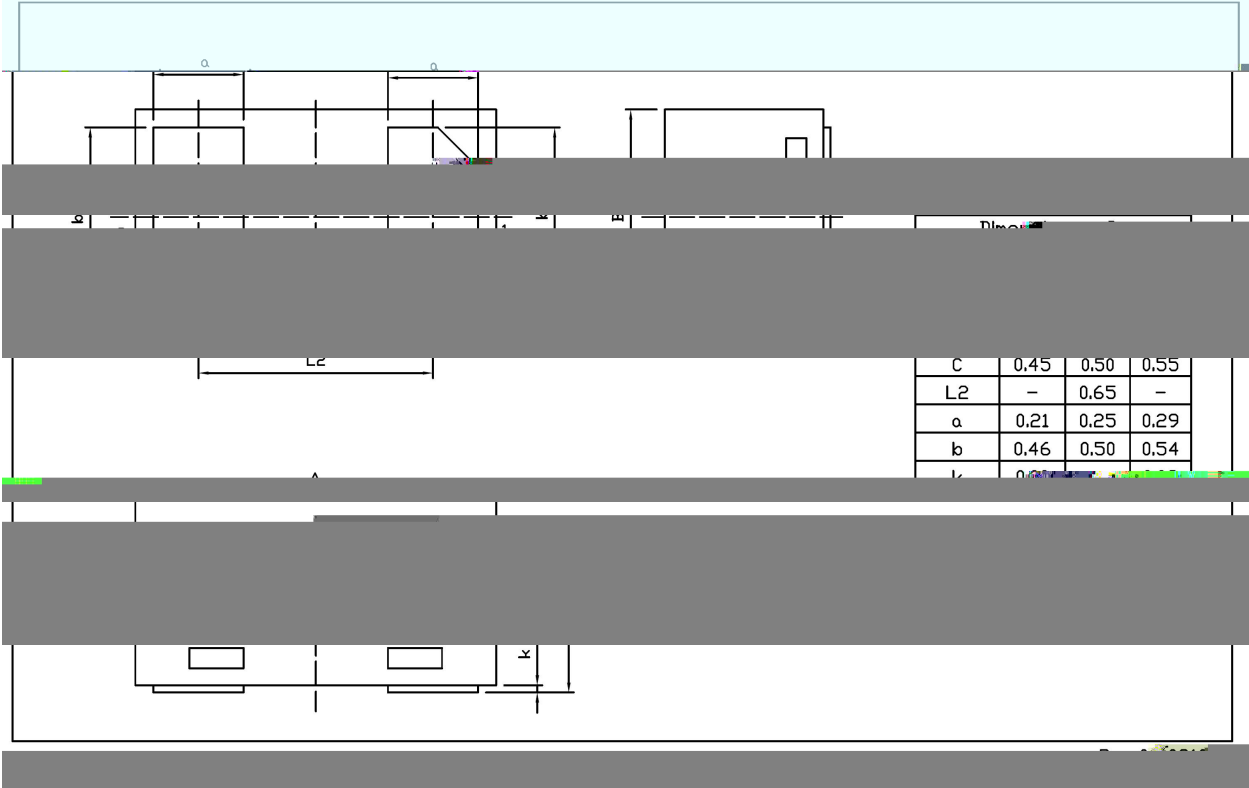
/ Electrical Characteristic Curve(Ta=25)



/ Package Dimensions

DFN1006-2L

Unit:mm



/ Marking Instructions



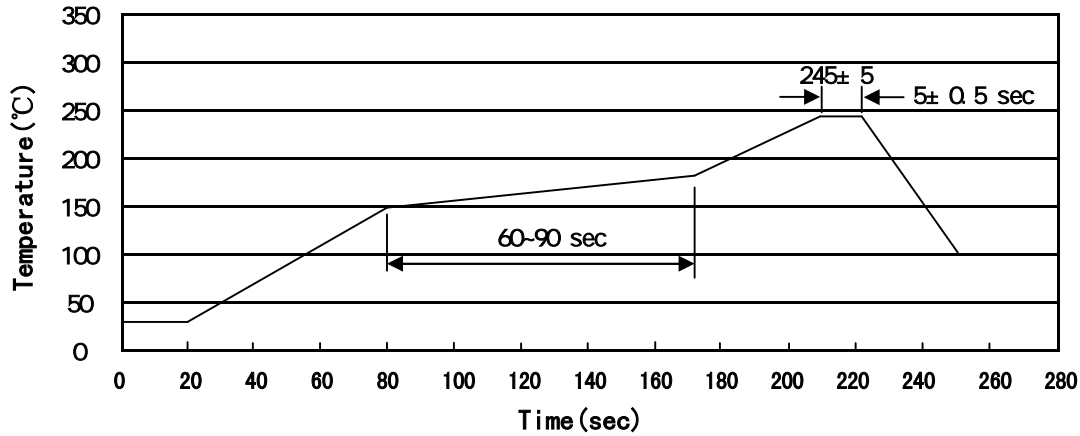
说明：

5B： 为型号代码

Note：

5B： Product Type.

() / Temperature Profile for IR Reflow Soldering(Pb-Free)



Note:

- 1 150 180 60 90sec; 1.Preheating:150~180 , Time:60~90sec.
- 2 245±5 5±0.5sec; 2.Peak Temp.:245±5 , Duration:5±0.5sec.
- 3 2 10 /sec. 3. Cooling Speed: 2~10 /sec.

/ Resistance to Soldering Heat Test Conditions

260±5 10±1 sec. Temp.:260±5℃ Time:10±1 sec

/ Packaging SPEC.

/ REEL

Package Type	Units					Dimension (unit mm ³)		
	Units/Reel 只/卷盘	Reels/Inner Box 卷盘/盒	Units/Inner Box 只/盒	Inner Boxes/Outer Box 盒/箱	Units/Outer Box 只/箱	Reel	Inner Box	Outer Box
DFN1006-2L	10,000	10	100,000	6	600,000	7" ×8	180×120×180	390×385×205

/ Notices